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Kind regards,

Team Nexperia

74VHC08; 74VHCT08

Quad 2-input AND gate

Rev. 01 — 30 June 2009

Product data sheet

1. General description

The 74VHC08; 74VHCT08 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard JESD7-A.

The 74VHC08; 74VHCT08 provide the quad 2-input AND function.

2. Features

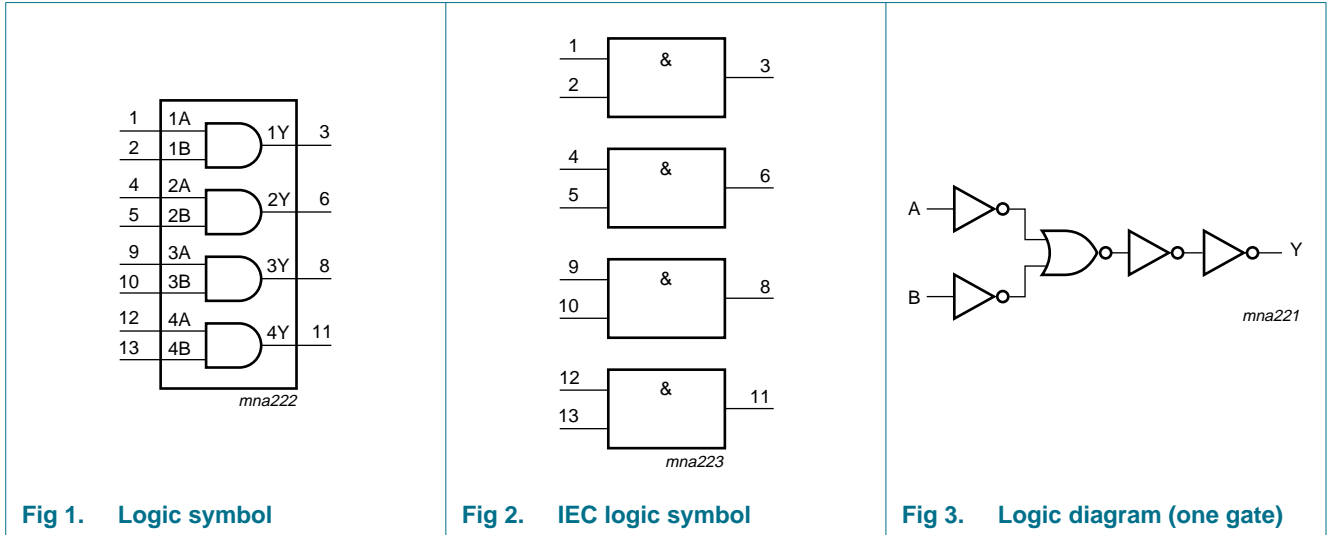
- Balanced propagation delays
- All inputs have a Schmitt-trigger action
- Inputs accepts voltages higher than V_{CC}
- Input levels:
 - ◆ The 74VHC08 operates with CMOS logic levels
 - ◆ The 74VHCT08 operates with TTL logic levels
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

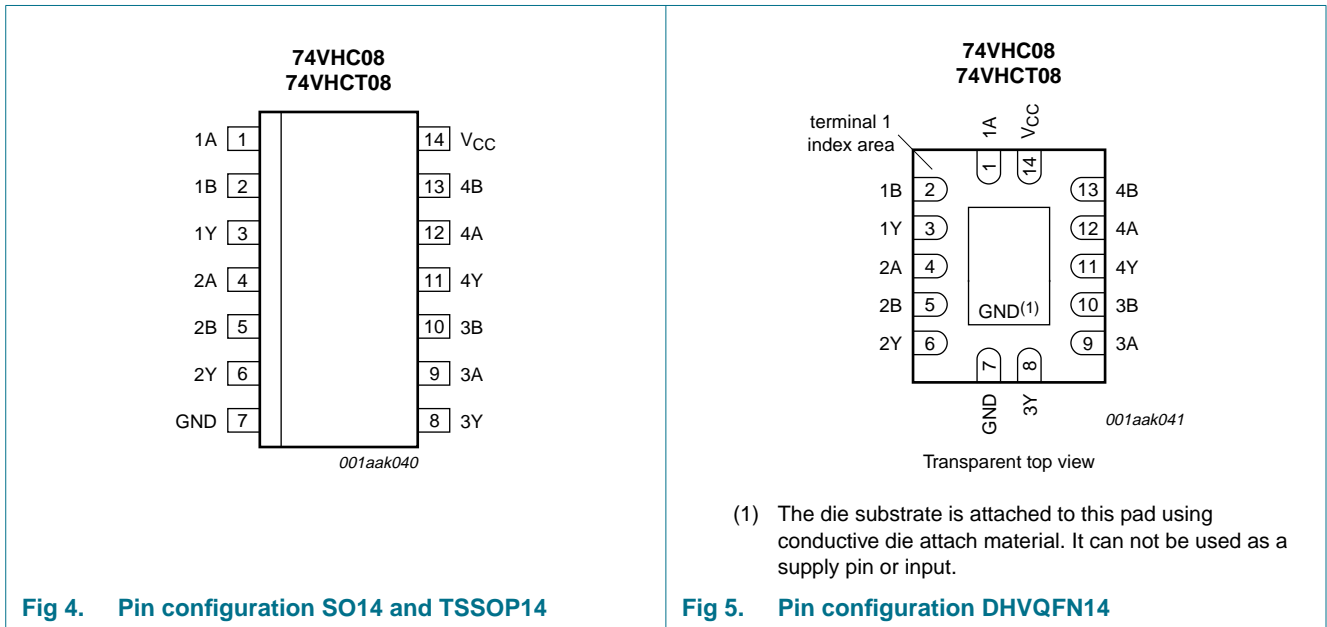
| Type number | Package | | | |
|-------------------------|-----------------------------------------------------------------|----------|------------------------------------------------------------------------------------------------------------------------------------------------|----------|
| | Temperature range | Name | Description | Version |
| 74VHC08D 74VHCT08D | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | SO14 | plastic small outline package; 14 leads; body width 3.9 mm | SOT108-1 |
| 74VHC08PW 74VHCT08PW | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | TSSOP14 | plastic thin shrink small outline package; 14 leads; body width 4.4 mm | SOT402-1 |
| 74VHC08BQ 74VHCT08BQ | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | DHVQFN14 | plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm | SOT762-1 |

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

| Symbol | Pin | Description |
|-----------------|-----|----------------|
| 1A | 1 | data input |
| 1B | 2 | data input |
| 1Y | 3 | data output |
| 2A | 4 | data input |
| 2B | 5 | data input |
| 2Y | 6 | data output |
| GND | 7 | ground (0 V) |
| 3Y | 8 | data output |
| 3A | 9 | data input |
| 3B | 10 | data input |
| 4Y | 11 | data output |
| 4A | 12 | data input |
| 4B | 13 | data input |
| V _{CC} | 14 | supply voltage |

6. Functional description

Table 3. Function selection^[1]

| Input | | Output |
|-------|----|--------|
| nA | nB | nY |
| L | X | L |
| X | L | L |
| H | H | H |

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|---------------------------------------------------------------------|---------|------|------|
| V _{CC} | supply voltage | | -0.5 | +7.0 | V |
| V _I | input voltage | | -0.5 | +7.0 | V |
| I _{IK} | input clamping current | V _I < -0.5 V | [1] -20 | - | mA |
| I _{OK} | output clamping current | V _O < -0.5 V or V _O > V _{CC} + 0.5 V | [1] - | ±20 | mA |
| I _O | output current | V _O = -0.5 V to (V _{CC} + 0.5 V) | - | ±25 | mA |
| I _{CC} | supply current | | - | 75 | mA |
| I _{GND} | ground current | | -75 | - | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|--------------------------------------|-----|-------|------|
| P _{tot} | total power dissipation | T _{amb} = -40 °C to +125 °C | | | |
| | SO14 package | | [2] | - 500 | mW |
| | TSSOP14 package | | [3] | - 500 | mW |
| | DHVQFN14 package | | [4] | - 500 | mW |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 74VHC08 | | | 74VHCT08 | | | Unit |
|------------------|-------------------------------------|---------------------------------|---------|-----|-----------------|----------|-----|-----------------|------|
| | | | Min | Typ | Max | Min | Typ | Max | |
| V _{CC} | supply voltage | | 2.0 | 5.0 | 5.5 | 4.5 | 5.0 | 5.5 | V |
| V _I | input voltage | | 0 | - | 5.5 | 0 | - | 5.5 | V |
| V _O | output voltage | | 0 | - | V _{CC} | 0 | - | V _{CC} | V |
| T _{amb} | ambient temperature | | -40 | +25 | +125 | -40 | +25 | +125 | °C |
| Δt/ΔV | input transition rise and fall rate | V _{CC} = 3.3 V ± 0.3 V | - | - | 100 | - | - | - | ns/V |
| | | V _{CC} = 5.0 V ± 0.5 V | - | - | 20 | - | - | 20 | ns/V |

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|--------|-----------|------------|-------|-----|-----|------------------|-----|-------------------|-----|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |

For type 74VHC08

| | | | | | | | | | | |
|-----------------|---------------------------------------------------|-----------------------------------------------------|------|-----|------|------|------|------|------|---|
| V _{IH} | HIGH-level input voltage | V _{CC} = 2.0 V | 1.5 | - | - | 1.5 | - | 1.5 | - | V |
| | | V _{CC} = 3.0 V | 2.1 | - | - | 2.1 | - | 2.1 | - | V |
| | | V _{CC} = 5.5 V | 3.85 | - | - | 3.85 | - | 3.85 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 2.0 V | - | - | 0.5 | - | 0.5 | - | 0.5 | V |
| | | V _{CC} = 3.0 V | - | - | 0.9 | - | 0.9 | - | 0.9 | V |
| | | V _{CC} = 5.5 V | - | - | 1.65 | - | 1.65 | - | 1.65 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = -50 μA; V _{CC} = 2.0 V | 1.9 | 2.0 | - | 1.9 | - | 1.9 | - | V |
| | | I _O = -50 μA; V _{CC} = 3.0 V | 2.9 | 3.0 | - | 2.9 | - | 2.9 | - | V |
| | | I _O = -50 μA; V _{CC} = 4.5 V | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.58 | - | - | 2.48 | - | 2.4 | - | V |
| | I _O = -8.0 mA; V _{CC} = 4.5 V | 3.94 | - | - | 3.8 | - | 3.7 | - | V | |

Table 6. Static characteristics ...continued
Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|--------------------------|---------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------|-------|-----|------|------------------|------|-------------------|------|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = 50 μA; V _{CC} = 2.0 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 50 μA; V _{CC} = 3.0 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 50 μA; V _{CC} = 4.5 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.36 | - | 0.44 | - | 0.55 | V |
| | | I _O = 8.0 mA; V _{CC} = 4.5 V | - | - | 0.36 | - | 0.44 | - | 0.55 | V |
| I _I | input leakage current | V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V | - | - | 0.1 | - | 1.0 | - | 2.0 | μA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V | - | - | 2.0 | - | 20 | - | 40 | μA |
| C _I | input capacitance | | - | 3.0 | 10 | - | 10 | - | 10 | pF |
| For type 74VHCT08 | | | | | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 4.5 V to 5.5 V | 2.0 | - | - | 2.0 | - | 2.0 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 4.5 V to 5.5 V | - | - | 0.8 | - | 0.8 | - | 0.8 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V | | | | | | | | |
| | | I _O = -50 μA | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -8.0 mA | 3.94 | - | - | 3.8 | - | 3.7 | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V | | | | | | | | |
| | | I _O = 50 μA | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 8.0 mA | - | - | 0.36 | - | 0.44 | - | 0.55 | V |
| I _I | input leakage current | V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V | - | - | 0.1 | - | 1.0 | - | 2.0 | μA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V | - | - | 2.0 | - | 20 | - | 40 | μA |
| ΔI _{CC} | additional supply current | per input pin; V _I = V _{CC} - 2.1 V; I _O = 0 A; other pins at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V | - | - | 1.35 | - | 1.5 | - | 1.5 | mA |
| C _I | input capacitance | | - | 3.0 | 10 | - | 10 | - | 10 | pF |

10. Dynamic characteristics

Table 7. Dynamic characteristics
GND = 0 V; For test circuit see Figure 7.

| Symbol | Parameter | Conditions | 25 °C | | | −40 °C to +85 °C | | −40 °C to +125 °C | | Unit |
|--------------------------|-------------------------------|-----------------------------------------------------------------------------------------|----------------|--------------------|------|------------------|------|-------------------|------|------|
| | | | Min | Typ ^[1] | Max | Min | Max | Min | Max | |
| For type 74VHC08 | | | | | | | | | | |
| t _{pd} | propagation delay | nA, nB to nY; see Figure 6 ^[2] V _{CC} = 3.0 V to 3.6 V | | | | | | | | |
| | | C _L = 15 pF | - | 4.0 | 8.8 | 1.0 | 10.5 | 1.0 | 11.0 | ns |
| | | C _L = 50 pF | - | 5.6 | 12.3 | 1.0 | 14 | 1.0 | 15.5 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | | | | | | | | |
| | | C _L = 15 pF | - | 3.0 | 5.9 | 1.0 | 7.0 | 1.0 | 7.5 | ns |
| | | C _L = 50 pF | | 4.2 | 7.9 | 1.0 | 9.0 | 1.0 | 10.0 | ns |
| C _{PD} | power dissipation capacitance | C _L = 50 pF; f _i = 1 MHz; V _i = GND to V _{CC} | ^[3] | - | 10.0 | - | - | - | - | pF |
| For type 74VHCT08 | | | | | | | | | | |
| t _{pd} | propagation delay | nA, nB to nY; see Figure 6 ^[2] V _{CC} = 4.5 V to 5.5 V | | | | | | | | |
| | | C _L = 15 pF | - | 3.2 | 6.9 | 1.0 | 8.0 | 1.0 | 9.0 | ns |
| | | C _L = 50 pF | - | 4.2 | 7.9 | 1.0 | 9.0 | 1.0 | 10.0 | ns |
| C _{PD} | power dissipation capacitance | C _L = 50 pF; f _i = 1 MHz; V _i = GND to V _{CC} | ^[3] | - | 12.0 | - | - | - | - | pF |

[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz, f_o = output frequency in MHz

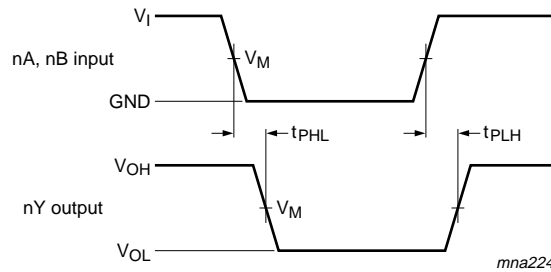
C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

11. Waveforms

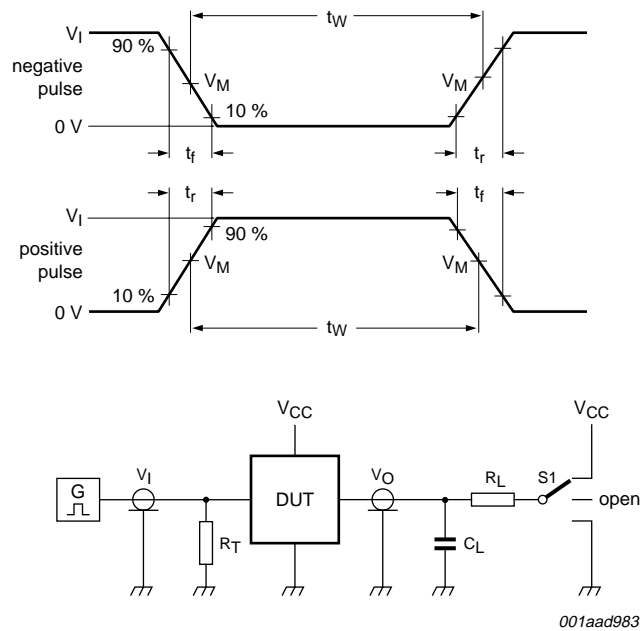


Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input (nA, nB) to output (nY) propagation delays

Table 8. Measurement points

| Type | Input | Output |
|----------|-------------|-------------|
| | V_M | V_M |
| 74VHC08 | $0.5V_{CC}$ | $0.5V_{CC}$ |
| 74VHCT08 | 1.5 V | $0.5V_{CC}$ |



001aad983

Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Load circuit for switching times

Table 9. Test data

| Type | Input | | Load | | S1 position | | |
|----------|----------|---------------|--------------|--------------|--------------------|--------------------|--------------------|
| | V_I | t_r, t_f | C_L | R_L | t_{PHL}, t_{PLH} | t_{PZH}, t_{PHZ} | t_{PZL}, t_{PLZ} |
| 74VHC08 | V_{CC} | ≤ 3.0 ns | 15 pF, 50 pF | 1 k Ω | open | GND | V_{CC} |
| 74VHCT08 | 3.0 V | ≤ 3.0 ns | 15 pF, 50 pF | 1 k Ω | open | GND | V_{CC} |

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

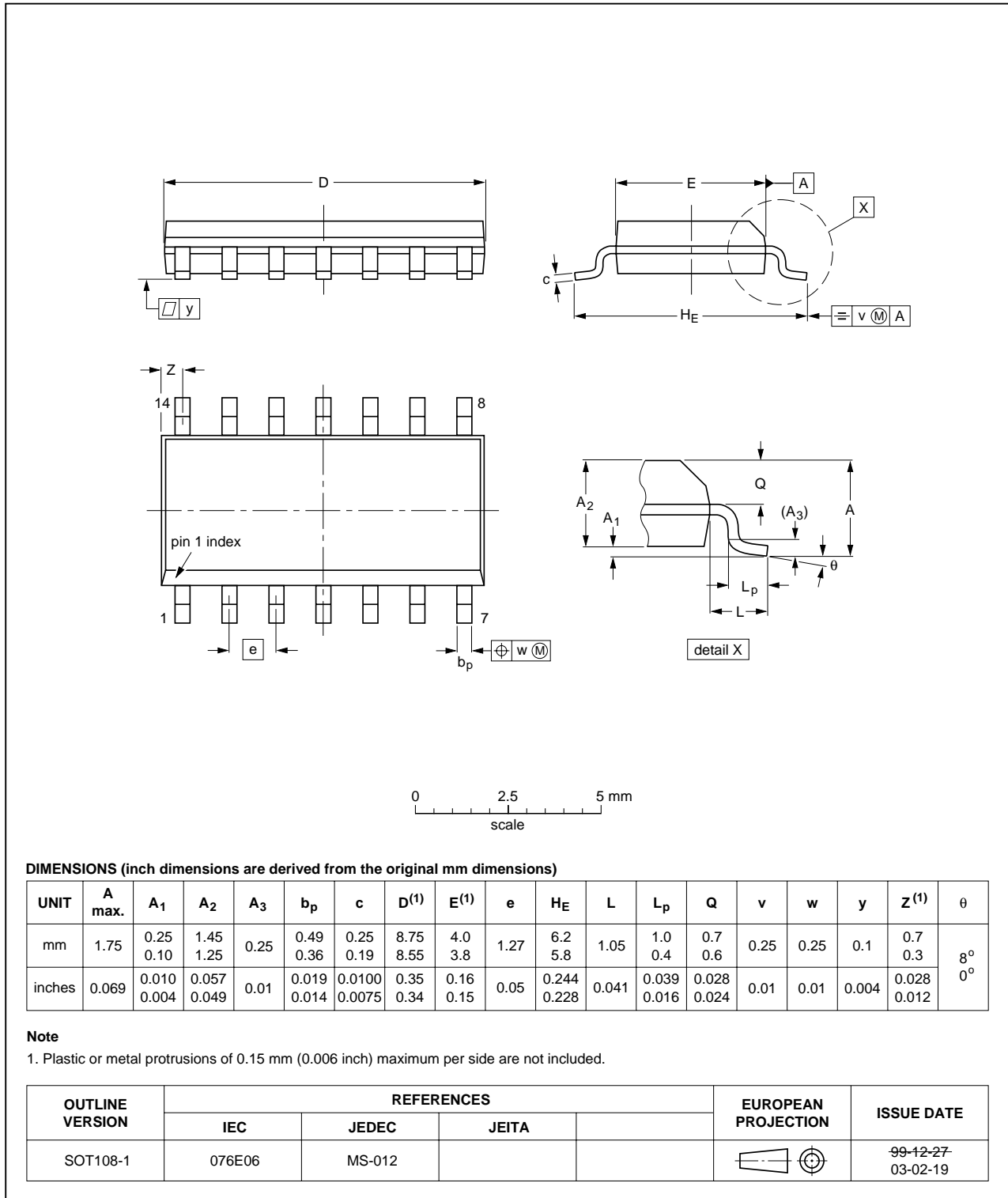


Fig 8. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

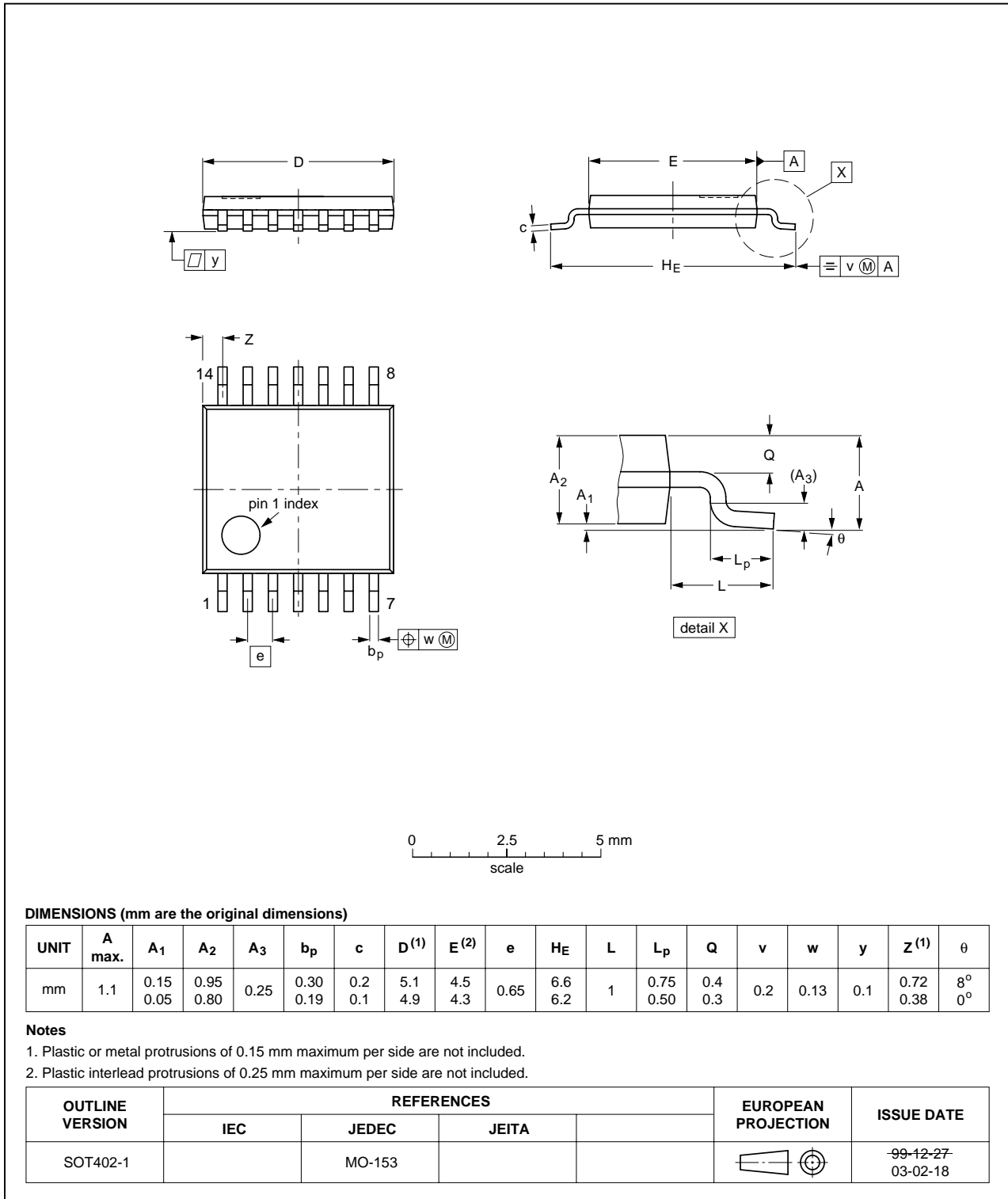


Fig 9. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

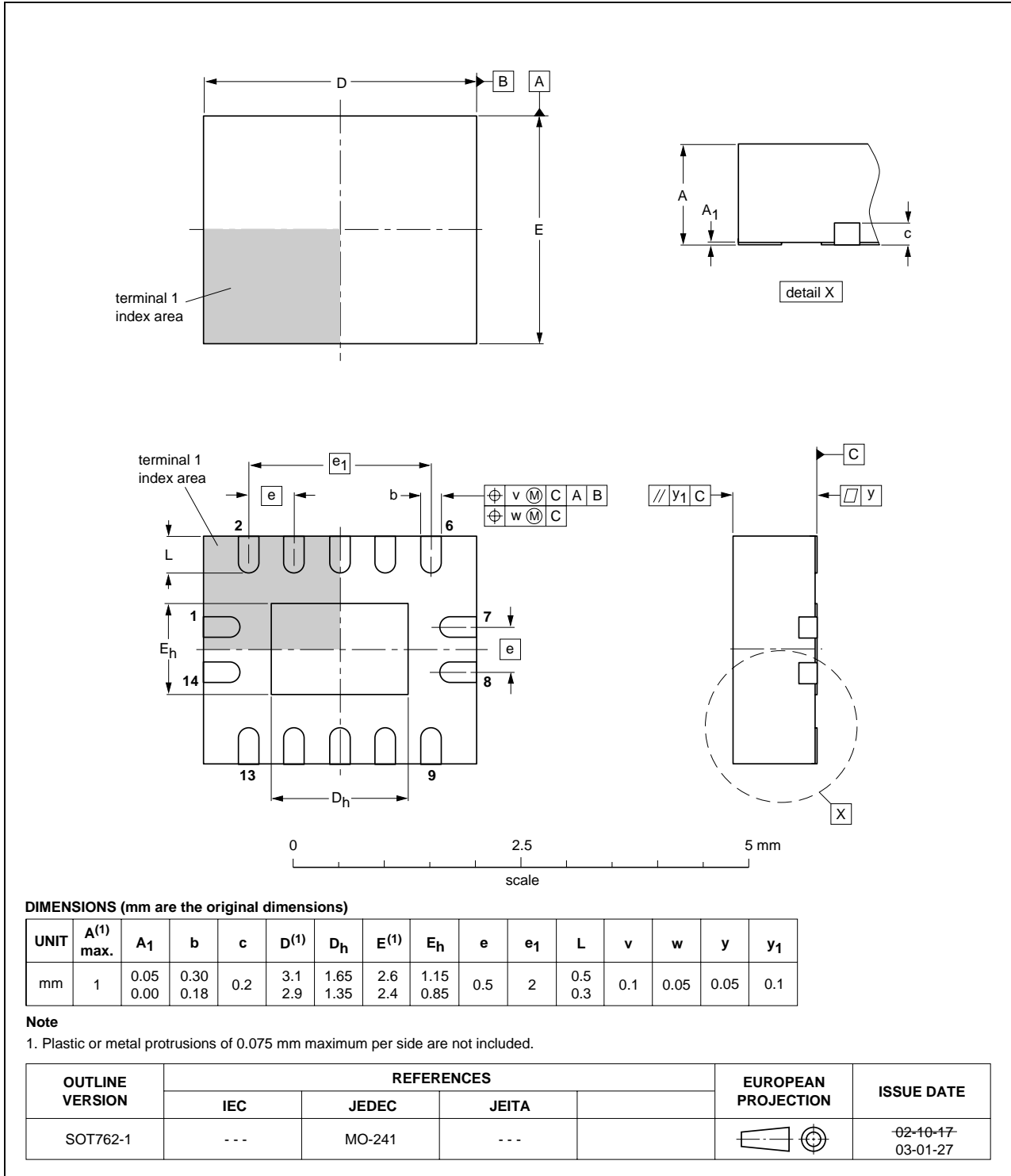


Fig 10. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

| Acronym | Description |
|---------|------------------------------------------------|
| CMOS | Complementary Metal Oxide Semiconductor |
| LSTTL | Low-power Schottky Transistor-Transistor Logic |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| MM | Machine Model |
| CDM | Charged Device Model |
| TTL | Transistor-Transistor Logic |

14. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| 74VHC_VHCT08_1 | 20090630 | Product data sheet | - | - |

15. Legal information

15.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
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